

【Abstract】

The present invention relates to an etching composition and a method for manufacturing a semiconductor device, using same. The etching composition comprises an inorganic acid and a silanol-based compound, wherein the silanol-based compound is
5 included in an amount of greater than or equal to 0.1 parts by weight and less than 10 parts by weight with respect to 100 parts by weight of the etching composition, and an APHA value of the etching composition is less than 1.5, and thus the etching composition can secure a sufficient etching selectivity ratio of a nitride film to an oxide film while suppressing abnormal growth in a high-temperature wet etching process, can prevent the generation of
10 bubbles immediately after preparation, thus not causing deterioration of etching process efficiency or damage to etching equipment, and exhibits almost no color, thus being more readily used during an etching process.

Fig.1